

**RECESSED TUNNEL OXIDE PROFILE FOR IMPROVED  
RELIABILITY IN NAND DEVICES**

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**ABSTRACT OF THE DISCLOSURE**

An improved NAND-type memory cell structure having improved reliability and endurance. Since a high risk area for oxide breakdown and/or current leakage exists in the tunnel oxide layer, source/drain overlap region, the present invention provides a NAND-type memory cell fabricated using controlled formation of the tunnel oxide layer.

531291 v1  
M-7468 US